



40V DUAL NPN SMALL SIGNAL TRANSISTOR IN SOT563

Features

- BV_{CEO} > 40V
- I_C = 200mA High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Finish; Solderable per MIL-STD-202, Method 208 (a3)
- Weight: 0.003 grams (Approximate)

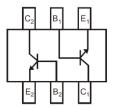
SOT563





Top View

Bottom View



Device Schematic Top View

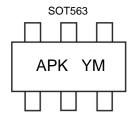
Ordering Information (Note 4)

Part Number	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT3904VC-7	Active	AEC-Q101	APK	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \text{APK} = \text{Product Type Marking Code} \\ \text{YM} = \text{Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: F} = 2018) \\ \text{M or } \overline{\text{M}} = \text{Month (ex: 9} = \text{September)} \end{array}$

Date Code Key

Year	2018		2019	2020		2021	2022		2023	2024		2025
Code	F		G	Н		I	J		K	L		J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	$V_{\sf CEO}$	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	Ι _C	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\Theta JA}$	833	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

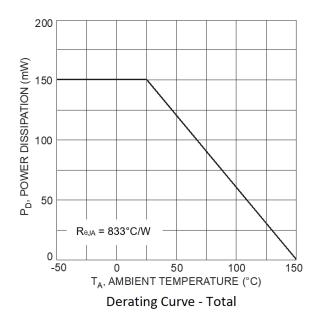
Notes:

^{5.} For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristic and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

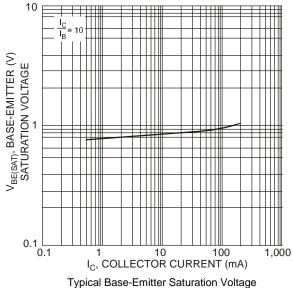
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS	OFF CHARACTERISTICS				
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	40	_	V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	_	V	$I_E = 100 \mu A, I_C = 0$
Collector-Emitter Cut-Off Current	I _{CEV}	_	50	nA	$V_{CE} = 30V$, $V_{EB(OFF)} = 3.0V$
Emitter-Base Cut-Off Current	I _{EBO}		50	nA	$V_{EB} = 6V$
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$I_C = 100\mu A, V_{CE} = 1.0V$ $I_C = 1.0mA, V_{CE} = 1.0V$ $I_C = 10mA, V_{CE} = 1.0V$ $I_C = 50mA, V_{CE} = 1.0V$ $I_C = 100mA, V_{CE} = 1.0V$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.20 0.30	٧	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65 —	0.85 0.95	٧	$I_C = 10mA$, $I_B = 1.0mA$ $I_C = 50mA$, $I_B = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{OBO}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	CIBO	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio	h _{re}	0.5	8.0	× 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f _T	300		MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0V$, $I_{C} = 100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_C = 10mA,$
Rise Time	t _r	_	35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t _f	_	50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$

Note:

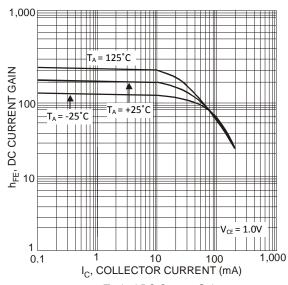
^{7.} Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



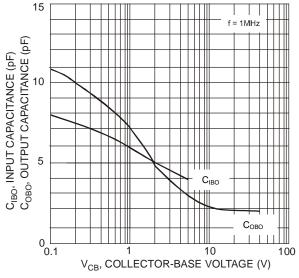
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



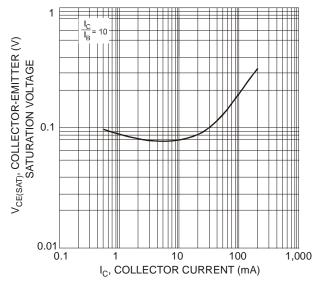
Typical Base-Emitter Saturation Voltage vs. Collector Current



Typical DC Current Gain vs. Collector Current



Input and Output Capacitance vs. Collector-Base Voltage

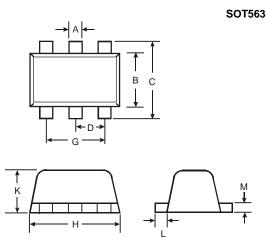


Typical Collector-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

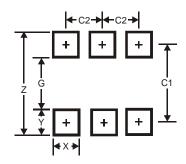


SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
М	0.10	0.18	0.11				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	SOT563
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5

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